IGBT

High speed IGBT in Trench and Fieldstop technology

IGA30N60H3

High speed switching series third generation

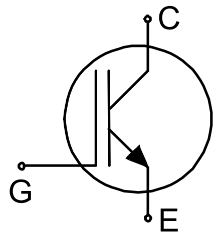
Datasheet

Industrial & Multimarket

High speed IGBT in Trench and Fieldstop technology

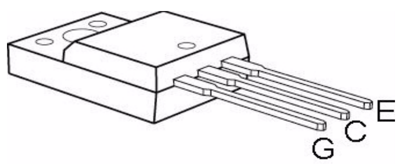
Features:

TRENCHSTOP™ technology offering
- very low V_{CEsat}
- low EMI
- maximum junction temperature 175°C
- qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- complete product spectrum and PSpice Models: http://www.infineon.com/igbt/



Applications:

- uninterruptible power supplies
- welding converters
- converters with high switching frequency



PG-TO-220-3 Fullpak

Key Performance and Package Parameters

Type	V_{CE}	I_C	V_{CEsat}, T_{vj}=25°C	T_{vjmax}	Marking	Package
IGA30N60H3	600V	30A	1.95V	175°C	G30H603	PG-TO220-3 FP

Table of Contents

Maximum ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	600	V
DC collector current, limited by T_{vjmax} T_C = 25°C T_C = 100°C	I_C	18.0 11.0	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	120.0	A
Turn off safe operating area V_{CE} ≤ 600V, T_{vj} ≤ 175°C	-	120.0	A
Gate-emitter voltage	V_{GE}	±20	V
Short circuit withstand time V_{GE} = 15.0V, V_{CC} ≤ 400V Allowed number of short circuits < 1000 Time between short circuits: ≥ 1.0s T_{vj} = 150°C	t_{SC}	5	µs
Power dissipation T_C = 25°C Power dissipation T_C = 100°C	P_{tot}	43.0 22.0	W
Operating junction temperature	T_{vj}	-40...+175	°C
Storage temperature	T_{stg}	-55...+150	°C
Soldering temperature, wave soldering 1.6 mm (0.063 in.) from case for 10s		260	°C
Mounting torque, M2.5 screw, TO220 Fullpak Maximum of mounting processes: 3 Mounting Torque, M3 Screw, other packages Maximum of mounting processes: 3	M	0.5 0.6	Nm
Isolation voltage for max. 60s, TO220 Fullpak	V_{isol}	2500	V

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance,[1)] junction - case	$R_{th(j-c)}$		3.50	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		65	K/W

[1)] Please be aware that in non standard load conditions, due to high Rth(j-c), Tvj close to Tvjmax can be reached.

Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE} = 0V, I_C = 2.00mA	600	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	V_{GE} = 15.0V, I_C = 30.0A T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 175°C	 - - -	 1.95 2.30 2.50	 2.40 - -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C = 0.43mA, V_{CE} = V_{GE}	4.1	5.1	5.7	V
Zero gate voltage collector current	I_{CES}	V_{CE} = 600V, V_{GE} = 0V T_{vj} = 25°C T_{vj} = 175°C	 - -	 - -	 40.0 1000.0	µA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0V, V_{GE} = 20V	-	-	100	nA
Transconductance	g_{fs}	V_{CE} = 20V, I_C = 30.0A	-	16.0	-	S

Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz	-	1630	-	pF
Output capacitance	C_{oes}		-	107	-	
Reverse transfer capacitance	C_{res}		-	50	-	
Gate charge	Q_G	V_{CC} = 480V, I_C = 30.0A, V_{GE} = 15V	-	165.0	-	nC
Short circuit collector current Max. 1000 short circuits Time between short circuits: ≥ 1.0s	$I_{C(SC)}$	V_{GE} = 15.0V, V_{CC} ≤ 400V, t_{SC} ≤ 5µs T_{vj} = 150°C	-	160	-	A

Switching Characteristic, Inductive Load, at T_{vj} = 25°C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 25°C, V_{CC} = 400V, I_C = 30.0A, V_{GE} = 0.0/15.0V, r_G = 10.5Ω, L_σ = 95nH, C_σ = 67pF L_σ, C_σ from Fig. E Energy losses include "tail" and diode (IKW30N60H3) reverse recovery.	-	18	-	ns
Rise time	t_r		-	22	-	ns
Turn-off delay time	$t_{d(off)}$		-	207	-	ns
Fall time	t_f		-	22	-	ns
Turn-on energy	E_{on}		-	0.73	-	mJ
Turn-off energy	E_{off}		-	0.44	-	mJ
Total switching energy	E_{ts}		-	1.17	-	mJ

Switching Characteristic, Inductive Load, at T_{vj} = 175°C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 175°C, V_{CC} = 400V, I_C = 30.0A, V_{GE} = 0.0/15.0V, r_G = 10.5Ω, L_σ = 95nH, C_σ = 67pF L_σ, C_σ from Fig. E Energy losses include "tail" and diode (IKW30N60H3) reverse recovery.	-	18	-	ns
Rise time	t_r		-	22	-	ns
Turn-off delay time	$t_{d(off)}$		-	239	-	ns
Fall time	t_f		-	23	-	ns
Turn-on energy	E_{on}		-	0.95	-	mJ
Turn-off energy	E_{off}		-	0.60	-	mJ
Total switching energy	E_{ts}		-	1.55	-	mJ

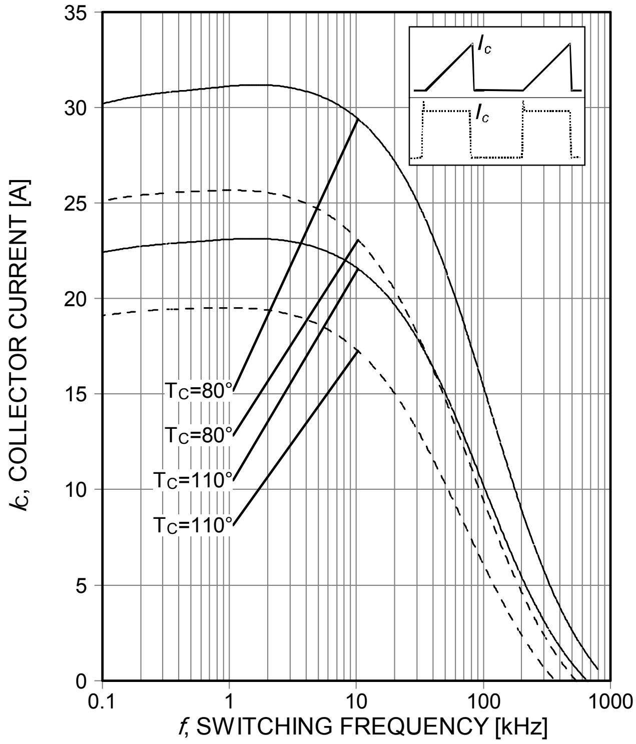


Figure 1. Collector current as a function of switching frequency
(T_j≤175°C, D=0.5, V_{CE}=600V, V_{GE}=15/0V, R_G=10,5Ω)

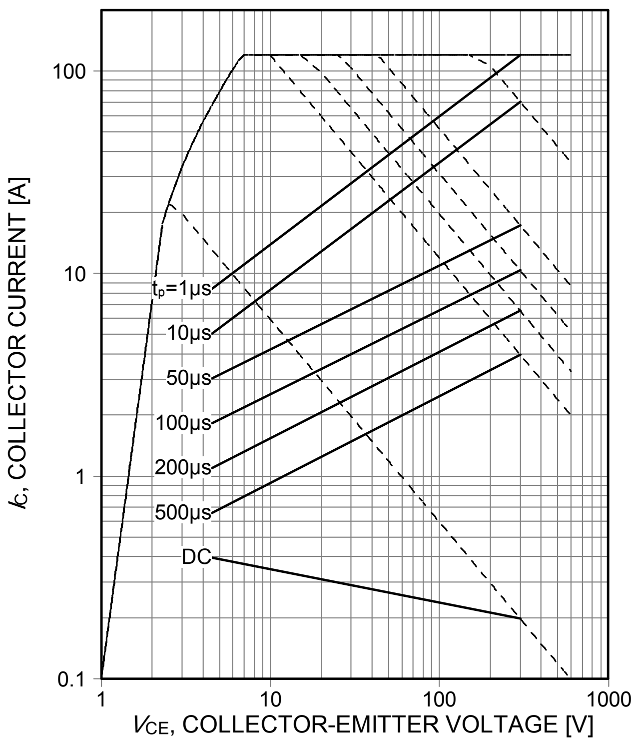


Figure 2. Forward bias safe operating area
(D=0, T_C=25°C, T_j≤175°C; V_{GE}=15V)

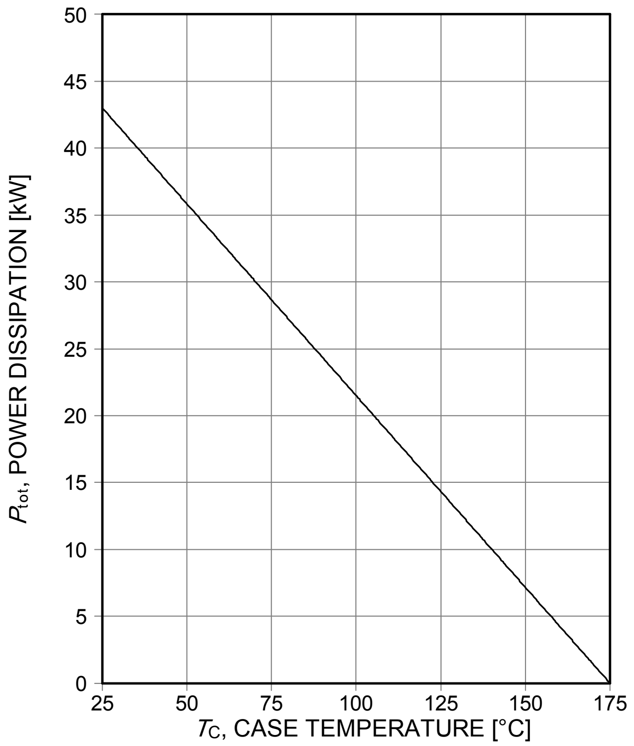


Figure 3. Power dissipation as a function of case temperature
(T_j≤175°C)

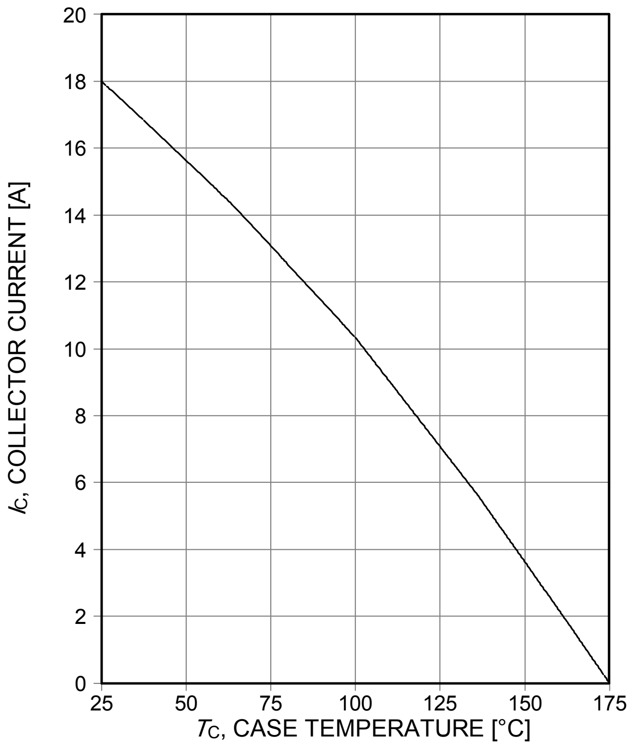


Figure 4. Collector current as a function of case temperature
(V_{GE}≥15V, T_j≤175°C)

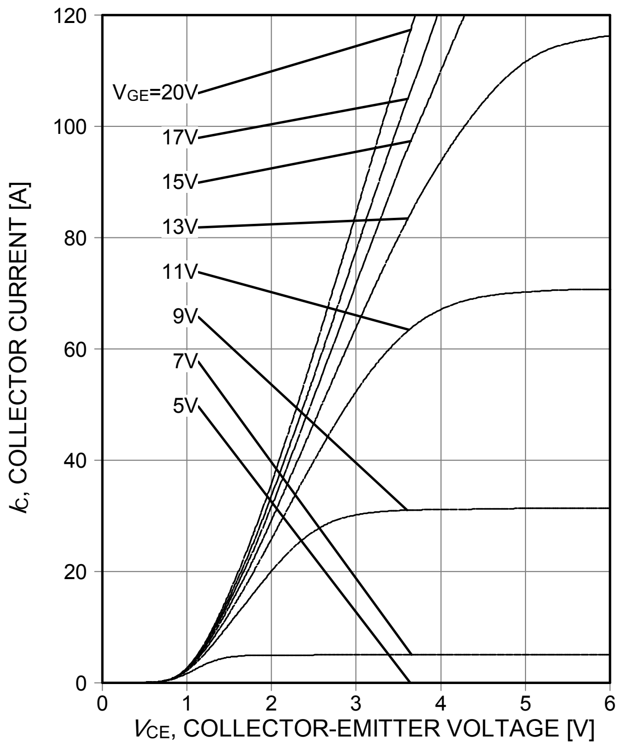


Figure 5. Typical output characteristic
(T_j=25°C)

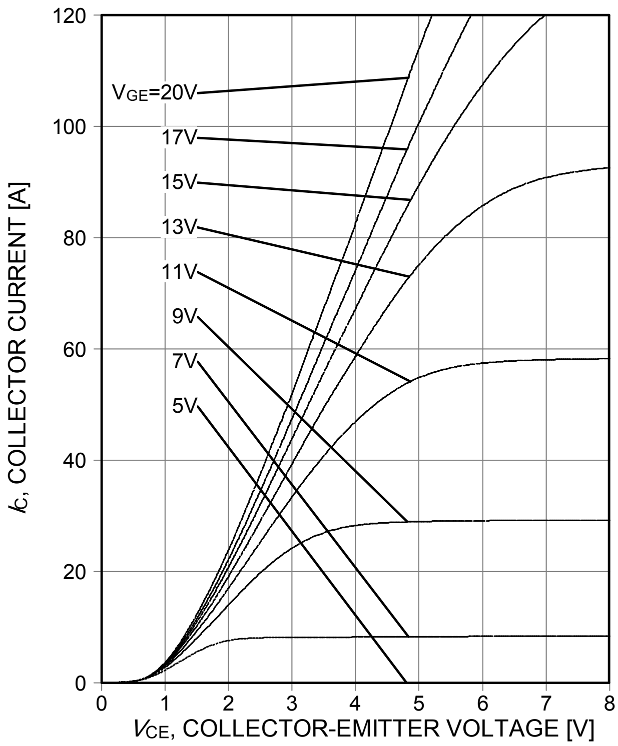


Figure 6. Typical output characteristic
(T_j=175°C)

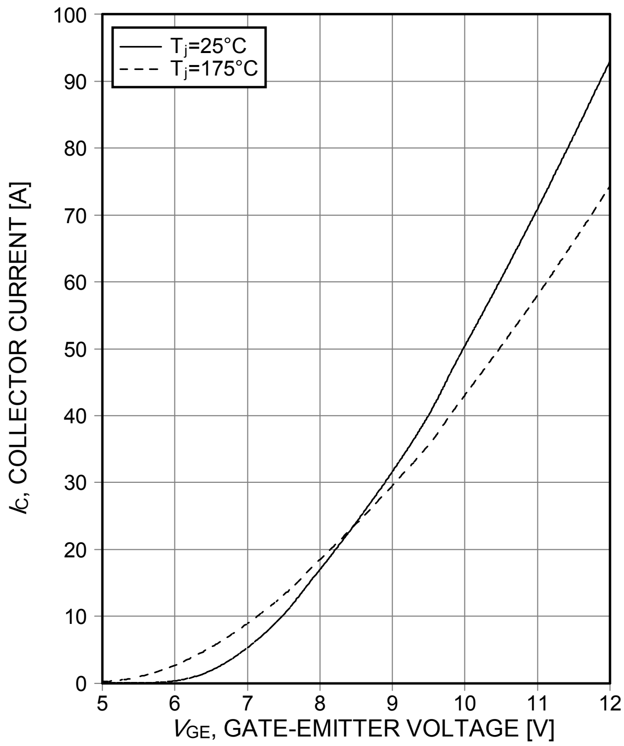


Figure 7. Typical transfer characteristic
(V_{CE}=20V)

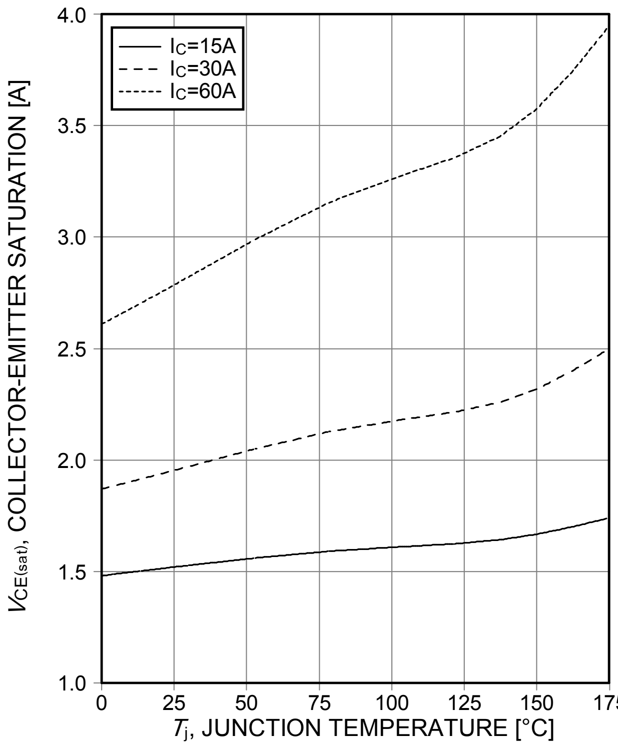


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
(V_{GE}=15V)

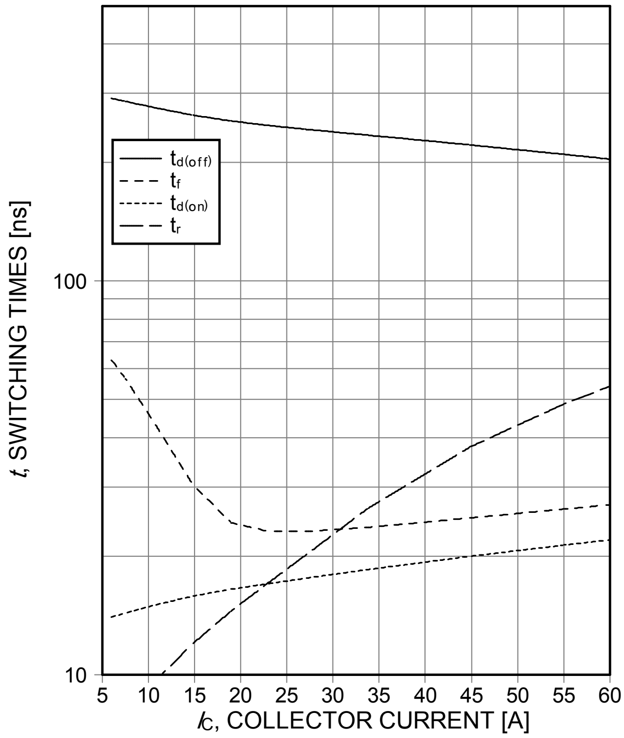


Figure 9. Typical switching times as a function of collector current
(ind. load, T_j=175°C, V_{CE}=400V, V_{GE}=15/0V, R_G=10,5Ω, test circuit in Fig. E)

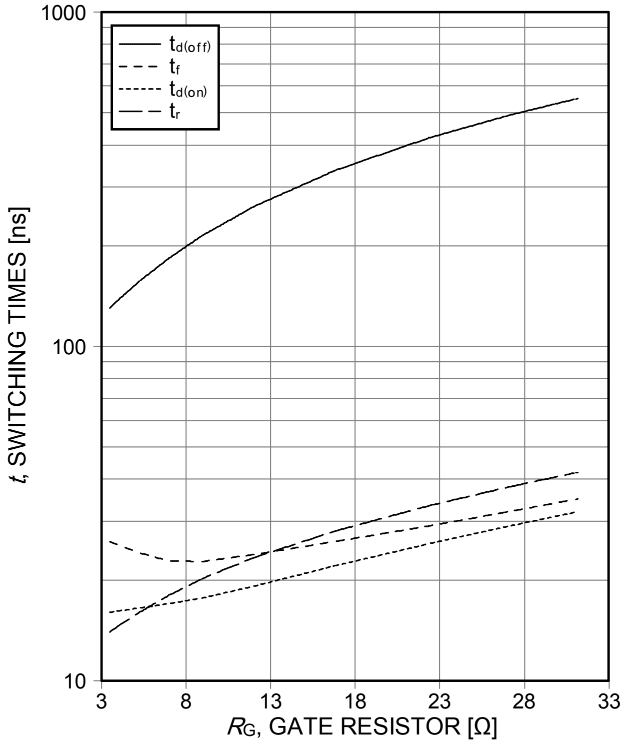


Figure 10. Typical switching times as a function of gate resistor
(ind. load, T_j=175°C, V_{CE}=400V, V_{GE}=15/0V, I_C=30A, test circuit in Fig. E)

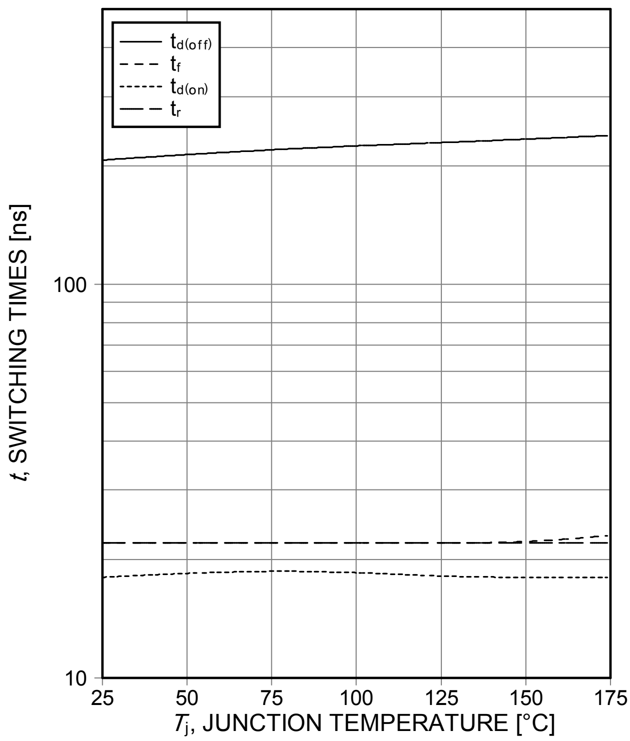


Figure 11. Typical switching times as a function of junction temperature
(ind. load, V_{CE}=400V, V_{GE}=15/0V, I_C=30A, R_G=10,5Ω, test circuit in Fig. E)

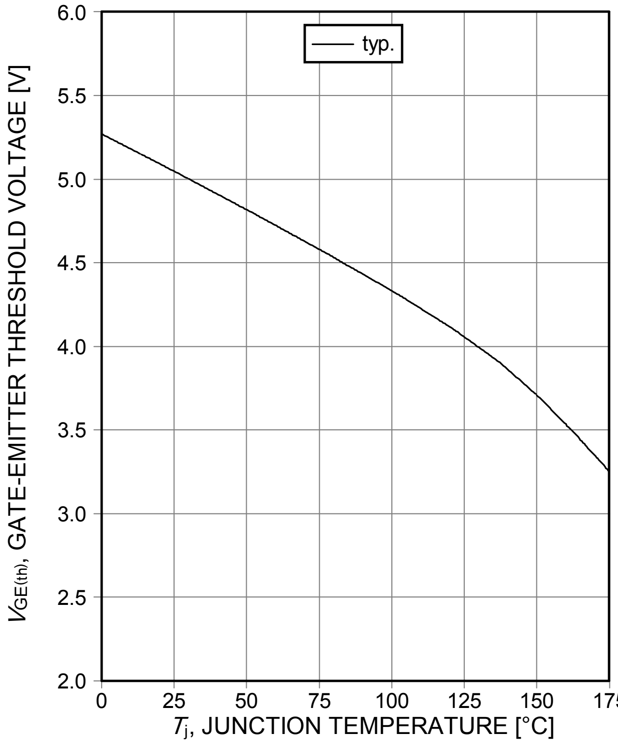


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
(I_C=0.43mA)

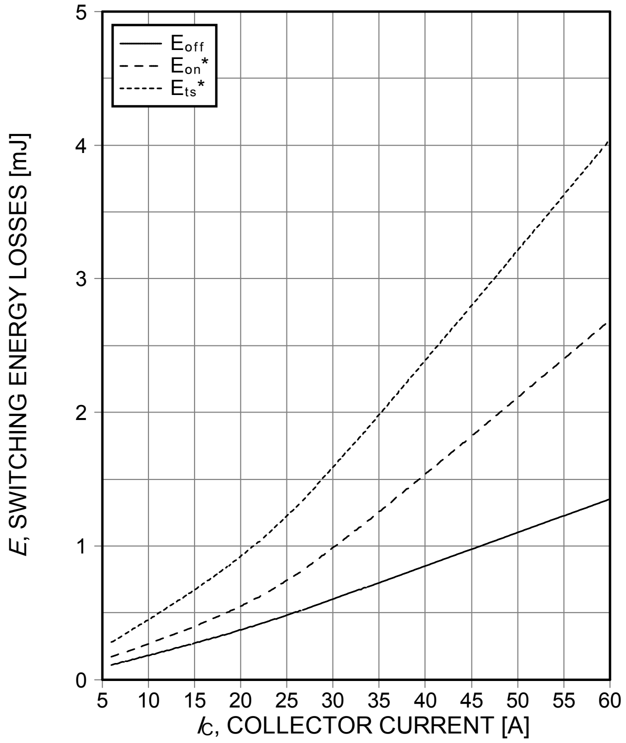


Figure 13. Typical switching energy losses as a function of collector current
(ind. load, T_j=175°C, V_{CE}=400V, V_{GE}=15/0V, R_G=10,5Ω, test circuit in Fig. E)

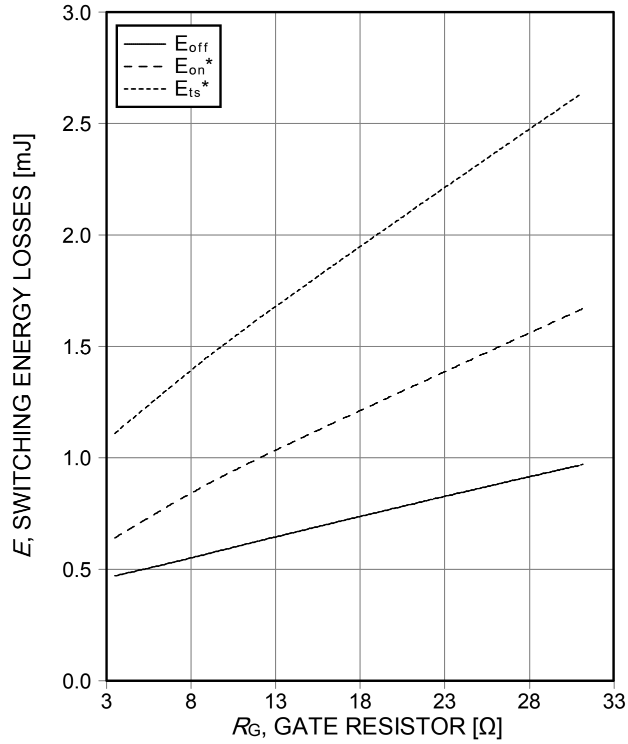


Figure 14. Typical switching energy losses as a function of gate resistor
(ind. load, T_j=175°C, V_{CE}=400V, V_{GE}=15/0V, I_C=30A, test circuit in Fig. E)

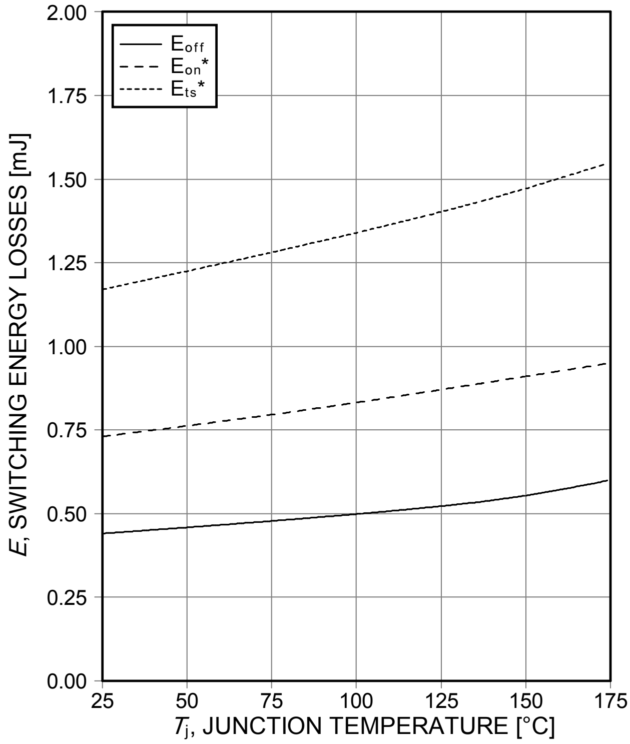


Figure 15. Typical switching energy losses as a function of junction temperature
(ind load, V_{CE}=400V, V_{GE}=15/0V, I_C=30A, R_G=10,5Ω, test circuit in Fig. E)

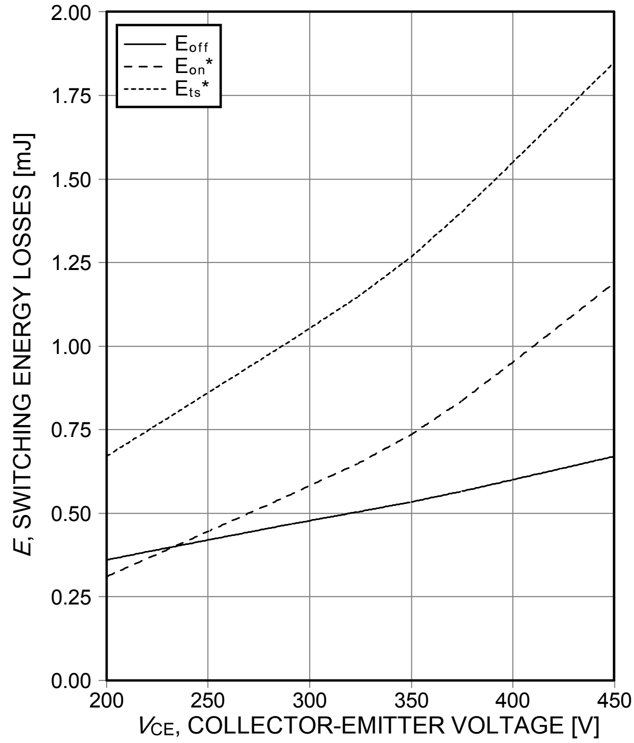


Figure 16. Typical switching energy losses as a function of collector emitter voltage
(ind. load, T_j=175°C, V_{GE}=15/0V, I_C=30A, R_G=10,5Ω, test circuit in Fig. E)

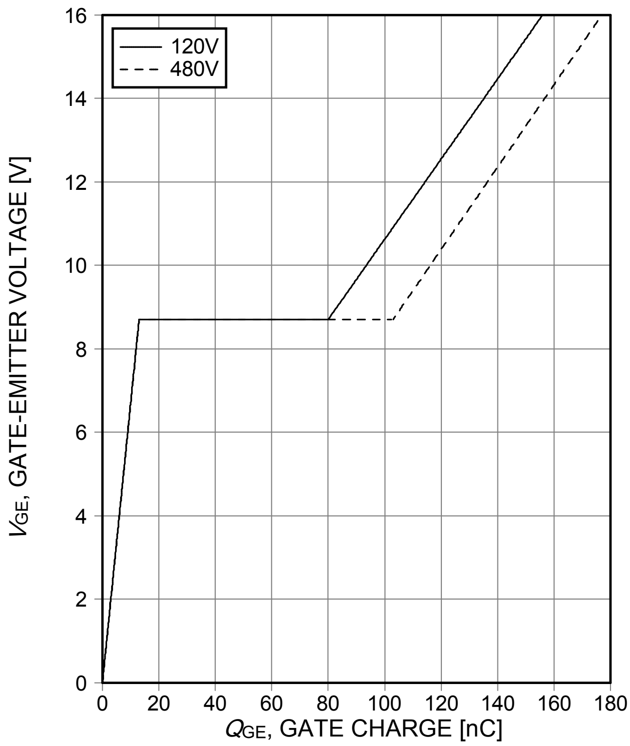


Figure 17. Typical gate charge
(I_C=30A)

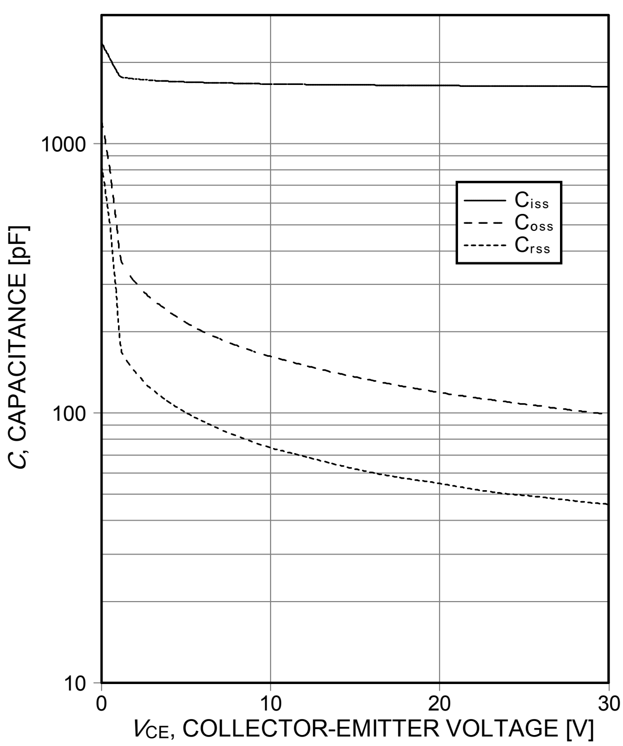


Figure 18. Typical capacitance as a function of collector-emitter voltage
(V_{GE}=0V, f=1MHz)

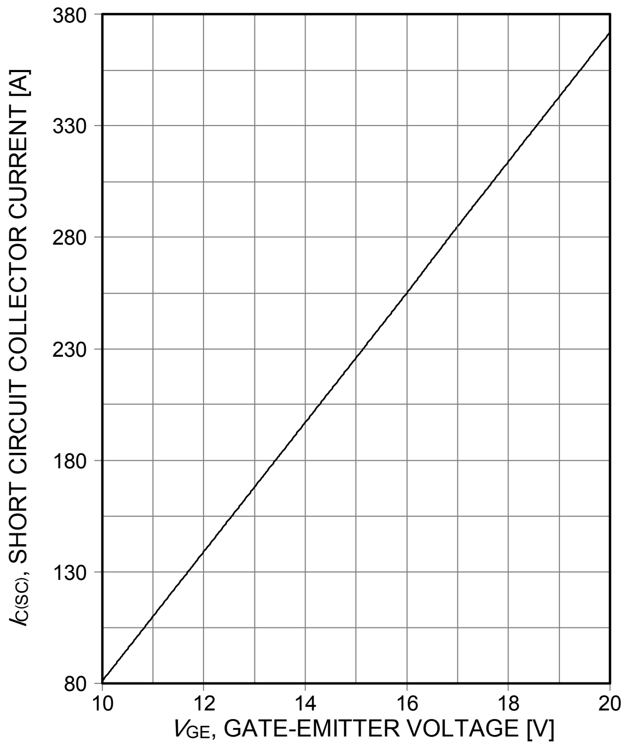


Figure 19. Typical short circuit collector current as a function of gate-emitter voltage
(V_{CE}≤400V, start at T_j=25°C)

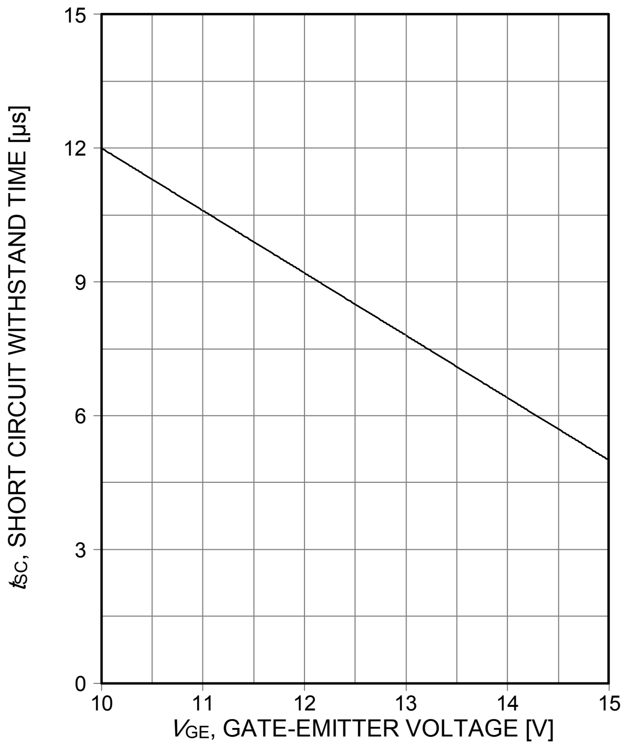


Figure 20. Short circuit withstand time as a function of gate-emitter voltage
(V_{CE}≤400V, start at T_j≤150°C)

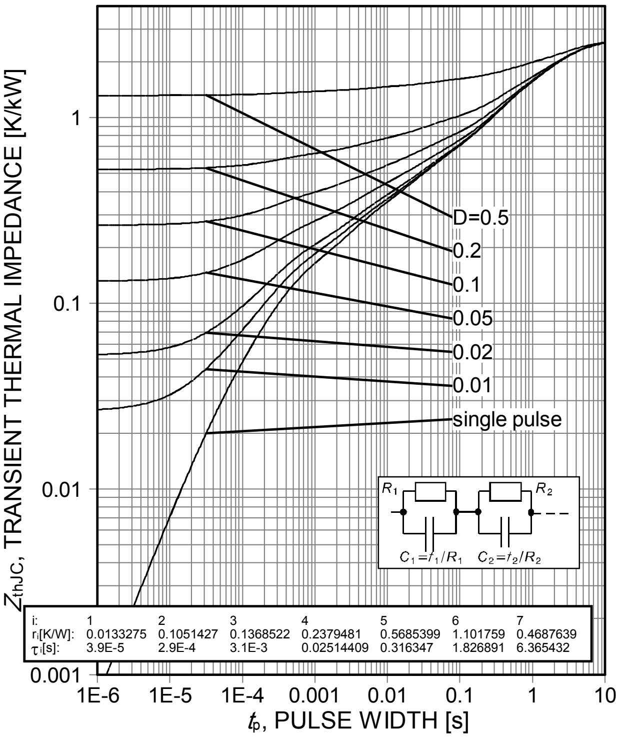
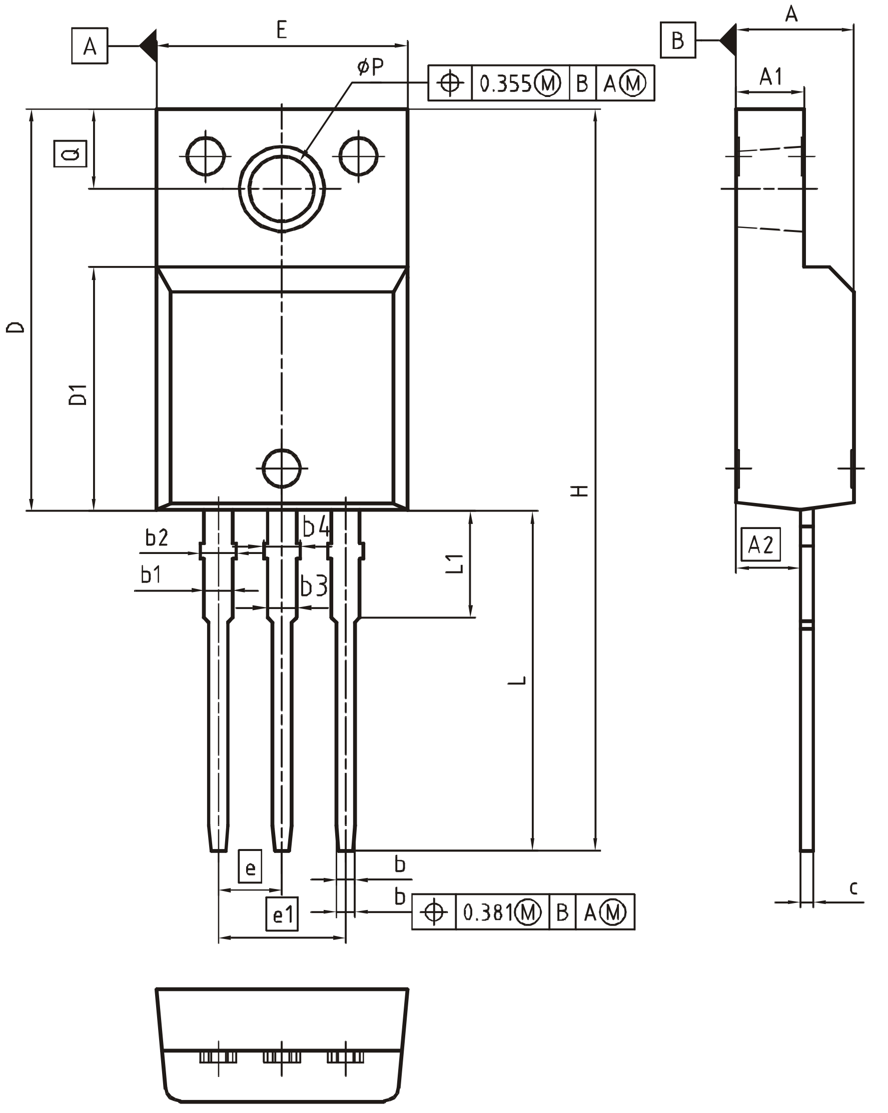


Figure 21. IGBT transient thermal impedance
($D=t_p/T$)

TO220-3-31/TO220-3-111



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.55	4.85	0.179	0.191
A1	2.55	2.85	0.100	0.112
A2	2.42	2.72	0.095	0.107
b	0.65	0.85	0.026	0.033
b1	0.95	1.33	0.037	0.052
b2	0.95	1.51	0.037	0.059
b3	0.65	1.33	0.026	0.052
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.85	16.15	0.624	0.636
D1	9.53	9.83	0.375	0.387
E	10.35	10.65	0.407	0.419
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H	29.45	29.75	1.159	1.171
L	13.45	13.75	0.530	0.541
L1	3.15	3.45	0.124	0.136
øP	2.95	3.20	0.116	0.126
Q	3.15	3.50	0.124	0.138

DOCUMENT NO.
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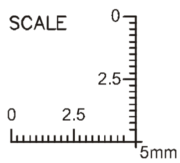
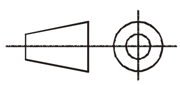
SCALE



EUROPEAN PROJECTION



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REVISION
03

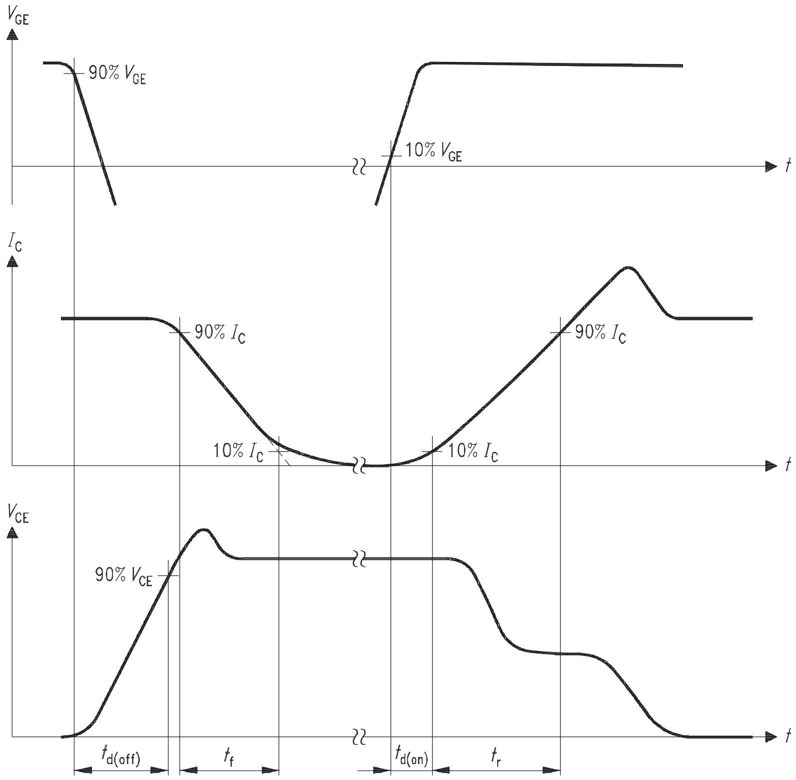

Figure A. Definition of switching times

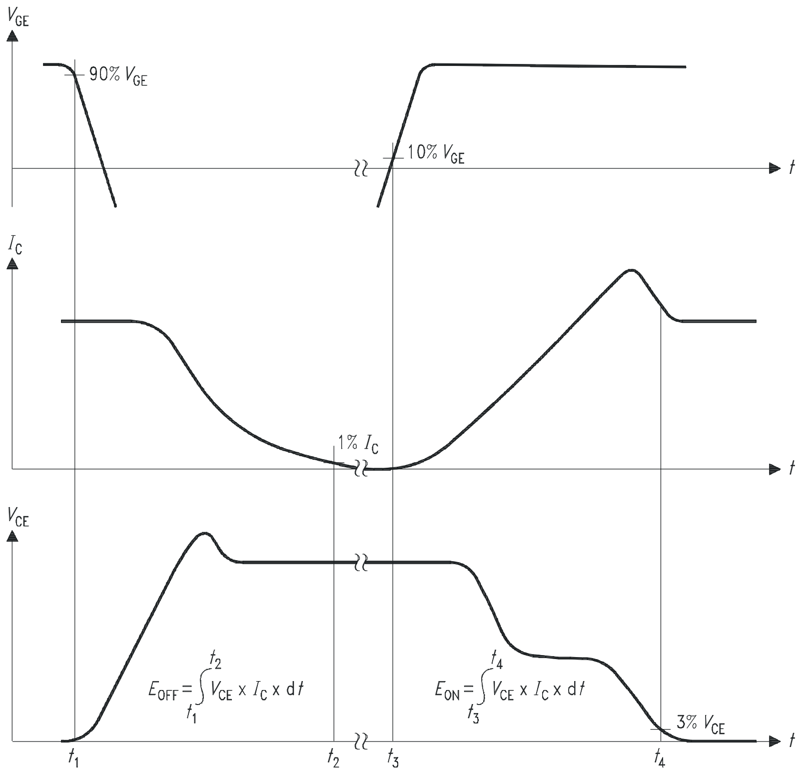

Figure B. Definition of switching losses

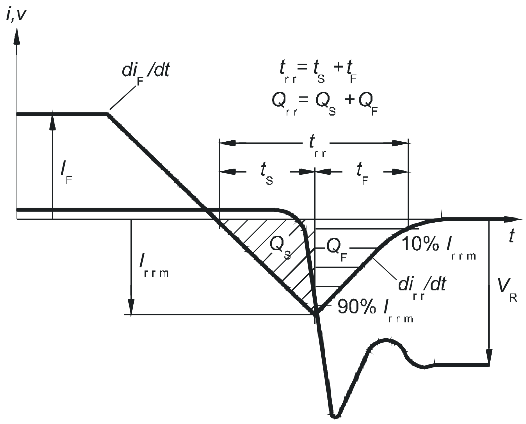

Figure C. Definition of diodes switching characteristics

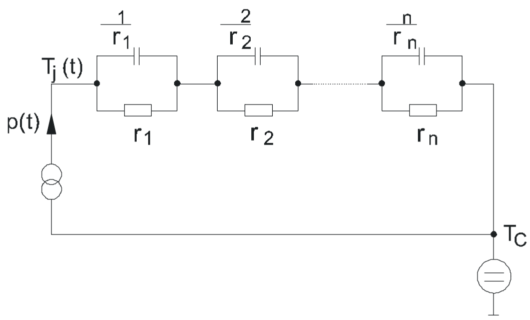

Figure D. Thermal equivalent circuit

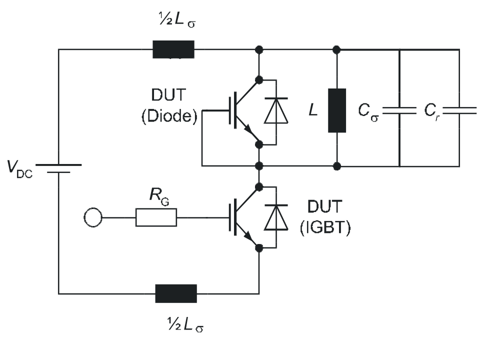

Figure E. Dynamic test circuit

Parasitic inductance L_σ,
Parasitic capacitor C_σ,
Relief capacitor C_r,
(only for ZVT switching)

Revision History

IGA30N60H3

Revision: 2010-07-21, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	-	Release of final datasheet

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